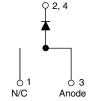


HEXFRED® Ultrafast Soft Recovery Diode, 4 A





TO-252AA (D-PAK)

• Ultı • Ultı • Ver

FEATURES

- · Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Guaranteed avalanche
- · Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

PRODUCT SUMMARY						
Package	TO-252AA (D-PAK)					
I _{F(AV)}	4 A					
V_R	600 V					
V _F at I _F	1.4 V					
t _{rr} typ.	17 ns					
T _J max.	150 °C					
Diode variation	Single die					

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V_{RRM}		600	V				
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4					
Single pulse forward current	I _{FSM}		25	Α				
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16					
Maximum power dissipation	P _D	T _C = 100 °C	10	W				
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +150	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS MIN. TYP.								
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-				
Forward voltage See fig. 1	V _F	I _F = 4 A	-	1.5	1.8	V			
		I _F = 8 A		1.8	2.2				
occ lig. 1		I _F = 4 A, T _J = 125 °C	-	1.4	1.7				
Maximum reverse	I _R	$V_R = V_R$ rated	-	0.17	3.0				
leakage current		$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	-	44	300	μA			
Junction capacitance	C _T	V _R = 200 V	-	4	8	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH			



DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		I _F = 1.0 A, dI _F /dt = 200 A/μA, V _R = 30 V		-	17	-			
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 4 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	28	42	ns		
		T _J = 125 °C		-	38	57			
Dools recovery average	I _{RRM}	T _J = 25 °C		-	2.9	5.2	А		
Peak recovery current		T _J = 125 °C		-	3.7	6.7			
Deverse receives abores	Q _{rr}	T _J = 25 °C		-	40	60	nC		
Reverse recovery charge		T _J = 125 °C		-	70	105	IIC		
Rate of fall of recovery current	dI _{(rec)M} /dt	T _J = 25 °C		-	280	-	Λ /ι ιο		
		T _J = 125 °C		-	235	-	A/μs		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	°C/W		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	- C/VV		
Majaht			-	2.0	-	g		
Weight			-	0.07	-	OZ.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style To-252AA (D-PAK)	HFA04SD60S					

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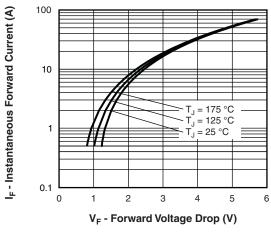


Fig. 1 - Typical Forward Voltage Drop Characteristics

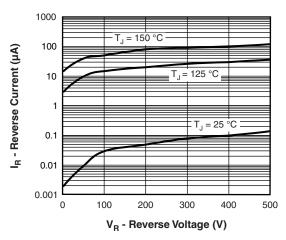


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

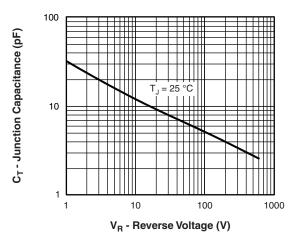


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

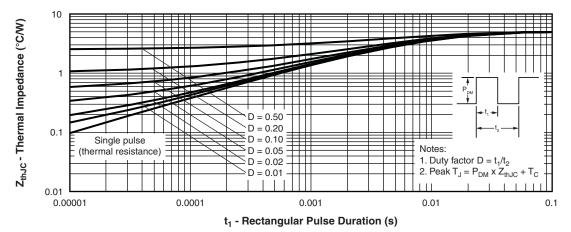


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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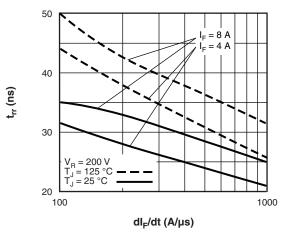


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

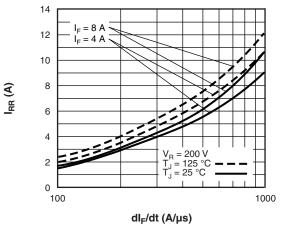


Fig. 6 - Typical Recovery Current vs. dl_F/dt

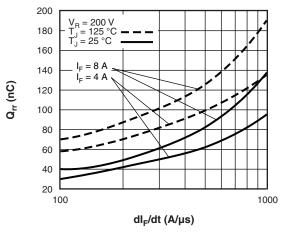


Fig. 7 - Typical Stored Charge vs. dl_F/dt

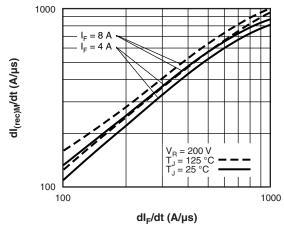


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

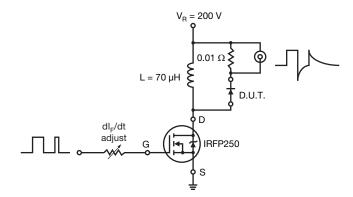
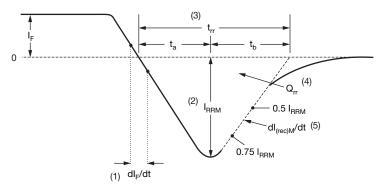


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

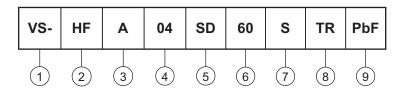
(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

- Current rating (04 = 4 A)

5 - D-PAK

6 - Voltage rating (60 = 600 V)

7 - S = D-PAK

8 - • TR = tape and reel

• TRR = tape and reel (right oriented)

• TRL = tape and reel (left oriented)

9 - • PbF = lead (Pb)-free

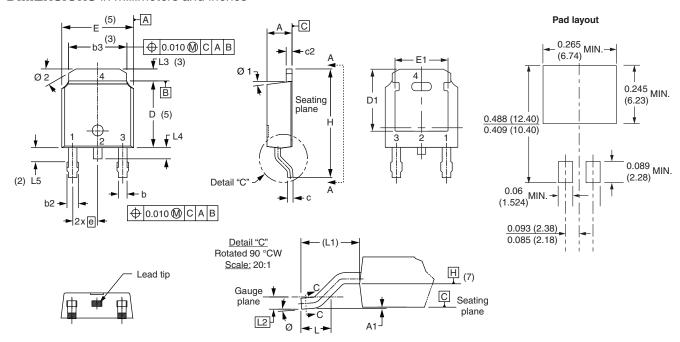
• P = lead (Pb)-free (for TRR and TRL)

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95016					
Part marking information	www.vishay.com/doc?95059					
Packaging information	www.vishay.com/doc?95033					



D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



	SYMBOL	MILLIMETERS		INC	HES	NOTES	SYMBOL	MILLIMETE	
	STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIDUL	MIN.
	А	2.18	2.39	0.086	0.094		е	2.29	BSC
	A1	-	0.13	-	0.005		Н	9.40	10
	b	0.64	0.89	0.025	0.035		L	1.40	1
	b2	0.76	1.14	0.030	0.045		L1	2.74	BSC
	b3	4.95	5.46	0.195	0.215	3	L2	0.51	BSC
	С	0.46	0.61	0.018	0.024		L3	0.89	1
	c2	0.46	0.89	0.018	0.035		L4	-	1
	D	5.97	6.22	0.235	0.245	5	L5	1.14	1
	D1	5.21	-	0.205	-	3	Ø	0°	1
	Е	6.35	6.73	0.250	0.265	5	Ø1	0°	1
	E1	4.32	-	0.170	-	3	Ø2	25°	3

SYMBOL	MILLIMETERS		INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
е	2.29	BSC	0.090	0.090 BSC	
Н	9.40	10.41	0.370	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		0.108	0.108 REF.	
L2	0.51 BSC		0.020	0.020 BSC	
L3	0.89	1.27	0.035	0.050	3
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	2
Ø	0°	10°	0° 10°		
Ø1	0°	15°	0°	15°	
Ø2	25°	35°	25°	35°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC outline TO-252AA



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